

DPS2024 Timetable

November 14 (Thu)	
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10:00	Registration
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Session A
AS1. Breakthrough process technology for advanced logic device fabrication

Keynote Presentation

Session B
Etching Technologies(1)

Session C
AS2. Atomic layer processes (ALE/ALD/ASD) for ultimate control of surface reaction(1)

November 15 (Fri)	
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Session D
AS2. Atomic layer processes (ALE/ALD/ASD) for ultimate control of surface reaction(2)

Session E
Surface Reaction and Damage

Session F
AS3. Understanding the mechanisms for future high-aspect-ratio etching technology

Session G
Computational Approaches

Session H
Plasma Diagnostics and Monitoring Systems

Session I
Dry process for Green Transformation:GX

Session J
Etching Technologies(2)

Session K
New Dry Process Concepts

Poster (120min)
Core-time (1) 10:40 -11:40 † Odd number
Core-time (2) 11:40 -12:40 † Even number

Lunch Break
12:40 - 13:40 (60min)

F-1 <Invited> Julian Schulze (Ruhr University Bochum)
"Knowledge based plasma control concepts for etching"

F-2 <Invited> Kukhan Yoon (Samsung Electronics Co., Ltd.)
"Challenges and Solutions for Fine Pitch High Aspect Ratio Contact Patterning in Sub-10nm DRAM"

Break 20min

G-1 Yuta Manabe (KIOXIA Corporation)
"Mitigation of twisting in low-temperature high-aspect-ratio etching using feature profile simulation"

G-2 Hojun Kang (Osaka Univ.)
"Computational study of High-Aspect-Ratio etching of SiO₂ by CF₃ + and WFS + ions"

H-1 Shunya Kawamura (Nagoya Univ.)
"Energy-resolved measurement of ion angular distribution in dual-frequency capacitively-coupled Ar plasma incident on an RF electrode"

I-1 Suzuka Okamoto (Daikin Industries, Ltd)
"Development of Low-GWP Gases for TSV Process Using Digital Twin"

I-2 Ah Hyun Park (The Univ. of Myongji)
"PECVD Chamber Cleaning with CO₂ for Alleviating Concerns on Global Warming Product"

Break 10min

J-1 Makoto Sekine (Nagoya Univ.)
"Cryogenic plasma etching of SiN films with HF-contained (CF₄/H₂, HF, H₂/Ar) gas mixtures"

J-2 Chih-Yu Ma (Nagoya Univ.)
"Cryogenic plasma etching of SiO₂ and Si using PF₃/H₂ precursors with different hydrogen concentrations"

K-1 Remi Dussart (GREMI - Université d'Orleans - CNRS)
"Cryogenic etching of SiO₂ and SiO_x in SF₆/H₂ plasma"

K-2 Thomas Tillocher (GREMI - Université d'Orleans - CNRS)
"Enhanced physisorption of CF radicals on Si surfaces cooled at cryogenic temperature and application to deep etching"

Closing Remarks (M. Kurihara, M. Jinno)